

Docket No. 210148US99

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Jamal RAMDANI, et al.

SERIAL NO: 09/885,409

GAU: 2812

FILED: June 21, 2001

EXAMINER: SIMKOVIC

FOR: METHOD FOR FABRICATING A SEMICONDUCTOR STRUCTURE INCLUDING A METAL OXIDE INTERFACE WITH SILICON



#7 / 1DS  
3-26-03  
Rothke

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were submitted in application Serial No. 09/908,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- ☒ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

03/19/2003 CV0111 00000160 09885409

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Respectfully submitted,

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Richard L. Treanor

Registration No. 36,379

Form PTO-122a  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

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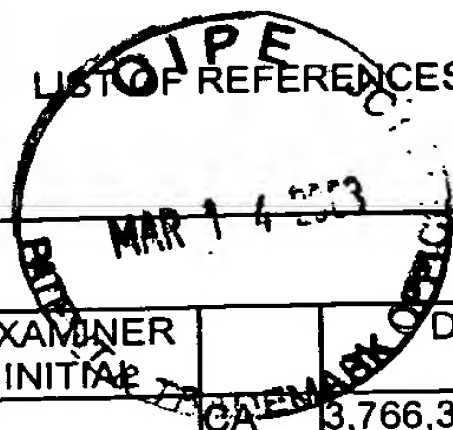
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LIST OF REFERENCES CITED BY APPLICANT

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastry			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Mantl et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
	BQ	6,180,486	01/30/01	Leobandung et al.			

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 210148US99		SERIAL NO. 09/885,409	
				APPLICANT Jamal RAMDANI, et al.			
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijaii et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
	DQ	6,222,654	04/24/01	Frigo			

Form PTO-1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

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2812

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
	FE	6,137,603	10/24/00	Henmi			
	FF	6,146,906	11/14/00	Inoue et al.			
	FG	6,173,474	01/16/01	Conrad			
	FH	6,180,252	01/30/01	Farrell et al.			
	FI	4,242,595	12/30/0	Lehovec			
	FJ	4,398,342	08/16/83	Pitt et al.			
	FK	4,424,589	01/03/84	Thomas et al.			
	FL	4,876,208	10/24/89	Gustafson et al.			
	FM	4,482,422	11/84	McGinn et al.			
	FN	4,667,088	05/19/87	Kramer			
	FO	4,772,929	09/20/88	Manchester et al.			
	FP	4,841,775	06/27/89	Ikeda et al.			
	FQ	4,845,044	07/04/89	Ariyoshi et al.			

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirrung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

Form PTB 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

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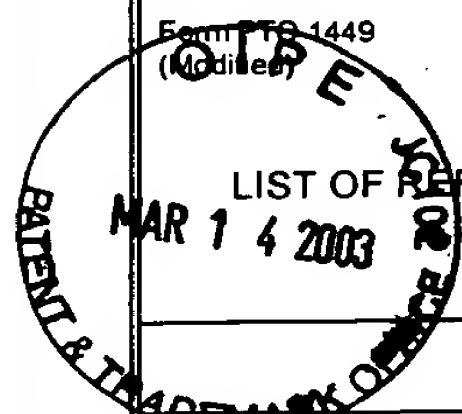
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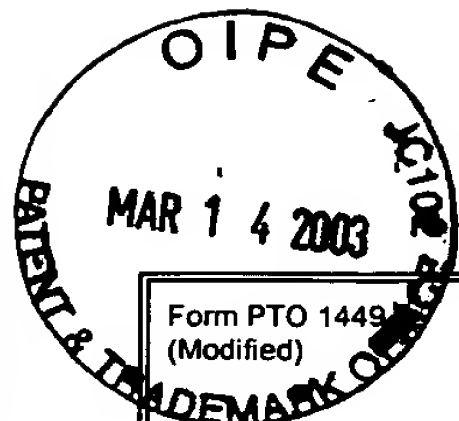
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## U.S. PATENT DOCUMENTS

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	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohori			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
	IX	5,872,493	02/16/99	Ella			
	IY	5,879,956	03/99	Seon et al.			
	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Partin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
	JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			
	JG	5,987,011	11/16/99	Toh			
	JH	6,022,140	02/08/00	Fraden et al.			
	JI	6,022,410	02/08/00	Yu et al.			
	JJ	6,023,082	02/08/00	McKee et al.			
	JK	6,028,853	02/22/00	Haartsen			
	JL	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al			
	JN	6,088,216	07/00	Laibowitz et al.			
	JO	6,090,659	07/00	Laibowitz et al.			
	JP	6,107,721	08/22/00	Lakin			
	JQ	6,153,010	11/28/00	Kiyoku et al			





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(Modified)U.S. DEPARTMENT OF COMMERCE  
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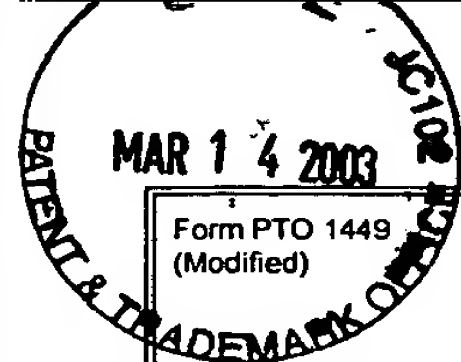
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al.			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
	KV	6,252,261	06/26/01	Usui et al.			
	KW	6,255,198	07/03/01	Linthicum et al.			
	KX	6,268,269	07/31/01	Lee et al.			
	KY	6,291,319	09/18/01	Yu et al.			
	KZ	6,316,785	11/13/01	Nunoue et al.			
	LA	6,343,171	01/29/02	Yoshimura et al.			
	LB	4,965,649	10/23/90	Zanio et al.			
	LC	6,253,649	05/01	Kawahara et al.			
	LD	6,211,096	04/01	Allman et al.			
	LE	6,239,449	05/29/01	Fafard et al.			
	LF	2001/0013313	08/16/01	Droopad et al.			
	LG	6,184,044	02/06/01	Sone et al.			
	LH	6,011,646	01/04/00	Mirkarimi et al.			
	LI	5,227,196	07/13/93	Itoh			
	LJ	6,150,239	11/21/00	Goesele et al.			
	LK	5,441,577	08/15/95	Sasaki et al.			
	LL	4,459,325	07/10/84	Nozawa et al.			
	LM	4,392,297	07/12/83	Little			
	LN	4,289,920	09/15/81	Hovel			
	LO	5,281,834	01/25/94	Cambou et al.			
	LP	4,901,133	02/13/90	Curran et al.			
	LQ	5,514,904	05/07/96	Onga et al.			

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	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			



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LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Jamal RAMDANI, et al.

FILING DATE

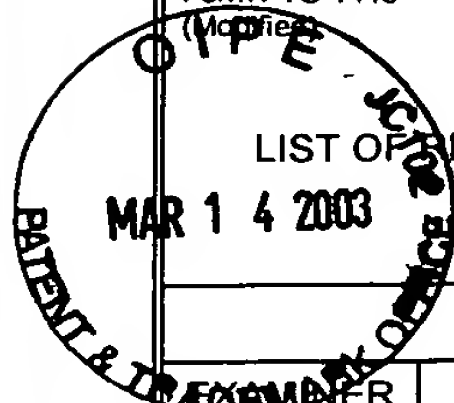
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2812

U.S. PATENT DOCUMENTS

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	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
	PE	6,210,988 B1	04/03/01	Howe et al.			
	PF	6,392,257	05/21/02	Ramdani et al.			
	PG	4,442,590	04/17/84	Stockton et al.			
	PH	5,603,764	02/18/97	Matsuda et al.			
	PI	6,087,681	06/11/00	Shakuda			
	PJ	5,132,648	07/21/92	Trinh et al.			
	PK	6,427,066	07/30/02	Grube			
	PL	2002/0072245	06/13/02	Ooms et al.			
	PM	6,278,138 B1	08/21/01	Suzuki			
	PN	5,888,296	03/30/99	Ooms et al.			
	PO	5,198,269	03/30/93	Swartz et al.			
	PP	2002/0030246	03/14/02	Eisenbeiser et al.			
	PQ	2002/0047143	04/25/02	Ramdani et al.			



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APPLICANT

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June 21, 2001

GROUP

2812

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	QA	5,776,359	07/07/98	Schultz et al.			
	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
	QQ	5,780,311	07/14/98	Beasom et al.			
	QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
	QS	5,399,898	03/21/95	Rostoker			
	QT	6,271,619	08/07/01	Yamada et al.			
	QU	5,334,556	08/02/94	Guldi			
	QV	4,910,164	03/20/90	Shichijo			
	QW	4,952,420	08/28/90	Walters			
	QX	6,121,647	09/19/00	Yano et al.			
	QY	6,306,668 B1	10/23/01	McKee et al.			
	QZ	6,143,366	11/07/00	Lu			
	RA	6,410,941	06/25/02	Taylor et al.			
	RB	5,397,428	03/14/95	Stoner et al.			
	RC	6,432,546 B1	08/13/02	Ramesh et al.			
	RD	6,345,424	02/12/02	Hasegawa et al.			
	RE	6,338,756 B2	01/15/02	Dietze			
	RF	5,516,725	05/14/96	Chang et al.			
	RG	4,667,212	05/19/87	Nakamura			
	RH	5,629,534	05/13/97	Inuzuka et al.			
	RI	3,914,137	10/21/75	Huffman et al.			
	RJ	5,753,928	05/19/98	Krause			
	RK	5,977,567	11/02/99	Verdiell			
	RL	5,130,762	07/14/92	Kulick			
	RM	5,621,227	04/15/97	Joshi			
	RN	6,389,209 B1	05/14/02	Suhir			
	RO	5,163,118	11/10/92	Lorenzo et al.			
	RP	5,926,493	07/20/99	O'Brien et al.			
	RQ	5,323,023	06/21/94	Fork			

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U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

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210148US99

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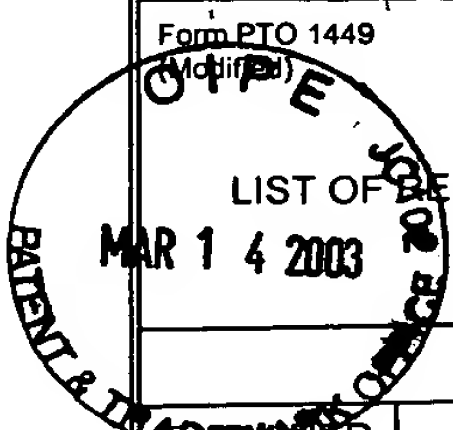
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## LIST OF REFERENCES CITED BY APPLICANT

## U.S. PATENT DOCUMENTS

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	SA	6,156,581	12/05/00	Vaudo et al.			
	SB	5,395,663	03/07/95	Tabata et al.			
	SC	4,146,297	03/27/79	Alferness et al.			
	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al			
	SJ	6,100,578	08/08/00	Suzuki			
	SK	6,410,947 B1	06/25/02	Wada			
	SL	6,417,059 B2	07/09/02	Huang			
	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
	SN	6,462,360 B1	10/08/02	Higgins, Jr. et al.			
	SO	5,981,976	11/09/99	Murasato			
	SP	5,981,980	11/09/99	Miyajima et al.			
	SQ	2002/0006245 A1	01/17/02	Kubota et al.			
	SR	2002/0131675 A1	09/19/02	Litvin			
	SS	6,256,426 B1	07/03/01	Duchet			
	ST	6,278,523 B1	08/21/01	Gorecki			
	SU	6,319,730 B1	11/20/01	Ramdani et al.			
	SV	6,404,027	06/11/02	Hong et al.			
	SW	6,312,819 B1	11/06/01	Jia et al.			
	SX	5,119,448	06/02/92	Schaefer et al.			
	SY	4,120,588	10/17/78	Chaum			
	SZ	5,194,917	03/16/93	Regener			
	TA	5,018,816	05/28/91	Murray et al.			
	TB	5,953,468	09/14/99	Finnila et al.			
	TC	5,561,305	10/01/96	Smith			
	TD	5,896,476	04/20/99	Wisseman et al.			
	TE	4,934,777	06/19/90	Jou et al.			
	TF	6,320,238 B1	11/20/01	Kizilyalli et al.			
	TG	6,393,167 B1	05/21/02	Davis et al.			
	TH	5,760,427	06/02/98	Onda			
	TI	6,411,756 B2	06/25/02	Sadot et al.			
	TJ	5,668,048	09/16/97	Kondo et al.			
	TK	5,852,687	12/22/98	Wickham			
	TL	5,122,852	06/16/92	Chan et al.			
	TM	5,173,835	12/22/92	Cornett et al.			
	TN	5,055,835	10/08/91	Sutton			
	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
	TQ	6,103,403	08/15/00	Grigorian et al.			



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PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

210148US99

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09/885,409

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Jamal RAMDANI, et al.

FILING DATE

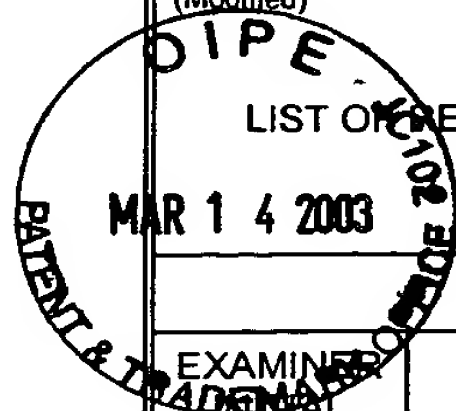
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2812

## U.S. PATENT DOCUMENTS

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	UA	5,635,433	06/03/97	Sengupta			
	UB	5,427,988	06/27/95	Sengupta et al.			
	UC	6,297,842 B1	10/02/01	Koizumi et al.			
	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
	UJ	5,995,528	11/30/99	Fukunaga et al.			
	UK	5,075,743	12/24/91	Behfar-Rad			
	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
	UO	6,278,137 B1	08/21/01	Shimoyama et al.			
	UP	5,623,439	04/22/97	Gotoh et al.			
	UQ	4,981,714	01/01/91	Ohno et al.			
	UR	6,194,753 B1	02/27/01	Seon et al.			
	US	6,326,637 B1	12/04/01	Parkin et al.			
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APPLICANT

Jamal RAMDANI, et al.

FILING DATE

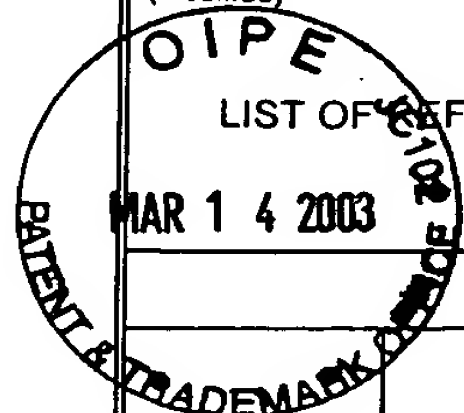
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	AAD	0 602 568	06/22/94	EP	X	
	AAE	0 607 435	07/27/94	EP	X	
	AAF	1 001 468	05/17/00	EP	X	
	AAG	0 514 018	11/19/92	EP	X	
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	AAI	1 319 311	06/04/70	Great Britain	X	
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	AAK	11-238683	08/31/99	Japan	X	
	AAL	11-260835	09/24/99	Japan w/English Abstract	X	
	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X	
	AAN	5-48072	02/26/93	Japan w/English Abstract	X	
	AAO	52-88354	07/23/77	Japan w/English Abstract	X	
	AAP	54-134554	10/19/79	Japan w/English Abstract	X	
	AAQ	55-87424	07/02/80	Japan w/English Abstract	X	
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	AAW	63-198365	08/17/88	Japan w/English Abstract	X	
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	ABA	WO 99/14804	03/25/99	WIPO	X	
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	ABC	WO 99/19546	04/22/99	WIPO		
	ABD	WO 00/33363	06/08/00	WIPO		
	ABE	WO 00/48239	08/17/00	WIPO		
	ABF	WO 99/14797	03/25/99	WIPO		
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	ABH	1 109 212	06/20/01	Europe		
	ABI	DE 197 12 496	10/30/97	Germany		X
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	ABK	60-210018	10/22/85	Japan w/English Abstract		
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	ABM	0 682 266	11/15/95	Europe		
	ABN	3-41783	02/91	Japan (English Abstract only)		
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APPLICANT

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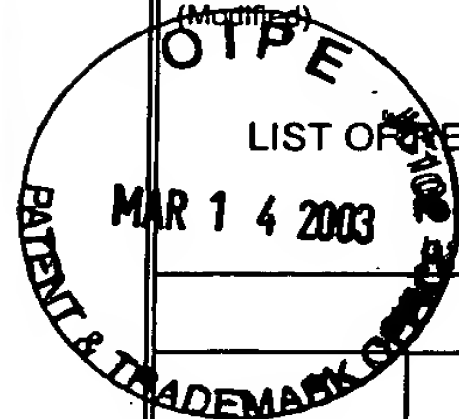
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## U.S. PATENT DOCUMENTS

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	BAB	2000-068466	03/00	Japan (Abstract)		
	BAC	64-50575	02/27/89	Japan		
	BAD	WO 98/05807	01/12/98	WIPO		
	BAE	WO 94/03908	02/17/94	WIPO		
	BAF	WO 01/33585	05/10/01	WIPO		
	BAG	1-102435	04/20/89	Japan w/English Abstract		
	BAH	52-135684	11/12/77	Japan (English Abstract)		
	BAI	02051220	02/21/90	Japan (English Abstract)		
	BAJ	11135614	05/21/99	Japan (w/English Abstract)		
	BAK	64-52329	02/28/89	Japan (w/English Abstract)		
	BAL	10-256154	09/25/98	Japan (w/English Abstract)		
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	BAX	0 964 453	12/15/99	Europe		
	BAY	5-152529	06/18/93	Japan w/English Abstract		
	BAZ	9-67193	03/11/97	Japan w/English Abstract		
	BBA	9-82913	03/28/97	Japan w/English Abstract		
	BBB	0 309 270	03/29/89	Europe		
	BBC	EP 0 957 522	11/17/99	Europe		
	BBD	EP 0 810 666	12/03/97	Europe		
	BBE	1-179411	07/17/89	Japan w/English Abstract		
	BBF	DE 100 17 137	10/26/00	GERMANY		
	BBG	WO 02 01648	01/03/02	WIPO		
	BBH	WO 02/33385 A2	04/25/02	WIPO		
	BBI	WO 01/59814 A2	08/16/01	WIPO		
	BBJ	WO 02/09160 A2	01/31/02	WIPO		
	BBK	WO 00/06812	02/10/00	WIPO		
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	BBM	0 538 611	04/28/93	Europe		
	BBN	WO 01/59820 A1	08/16/01	WIPO		
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	BBP	2 779 843	12/17/99	France		xx
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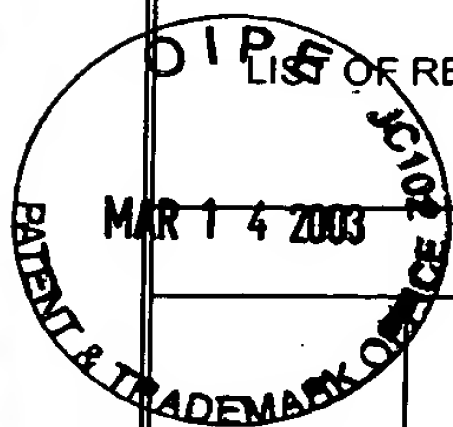
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## LIST OF REFERENCES CITED BY APPLICANT

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CAD	WO 02/03467	01/10/02	WIPO		
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CAF	61-36981	02/21/86	Japan w/English Abstract		
CAG	WO 93/07647	04/15/93	WIPO		
CAH	2002-9366	01/11/02	Japan w/English Abstract		
CAI	EP 0 881 669	12/02/98	Europe		
CAJ	WO 02/03480	01/10/02	WIPO		
CAK	WO 02/50879	06/27/02	WIPO		
CAL	EP 0 777 379	06/04/97	Europe		
CAM	WO 01/04943 A1	01/18/01	WIPO		xx
CAN	WO 02/47127 A2	06/13/02	WIPO		
CAO	JP 58-075868	05/07/83	Japan w/English Abstract		
CAP	EP 0 993 027	04/12/00	Europe		
CAQ	EP 0 711 853	05/15/96	Europe		
CAR	WO 98/20606	05/14/98	WIPO		
CAS	EP 1 043 765	10/11/00	Europe		
CAT	0 300 499	01/25/89	Europe		
CAU	EP 1 085 319	03/21/01	Europe		
CAV	WO 01/16395	03/08/01	WIPO		
CAW	2000-351692	12/19/00	Japan w/English Abstract		
CAX	03-188619	08/16/91	Japan (English Abstract only)		
CAY	63-289812	11/28/88	Japan (English Abstract only)		
CAZ	EP 0 884 767	12/16/98	Europe		
CBA	06-069490	03/11/94	Japan (English Abstract only)		
CBB	WO 01/59821 A1	08/16/01	WIPO		
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2812

LIST OF REFERENCES CITED BY APPLICANT

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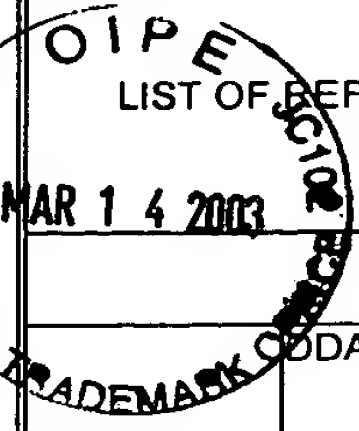
## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

CCAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO <sub>3</sub> Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.
CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.
CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", <i>1998 Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.
CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.
CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO <sub>3</sub> Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.
CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.
CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," <i>1997 Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.
CCAH	A. Mansingh et al., "Surface Acoustic Wave Propagation in PZT/YBCO/SrTiO <sub>3</sub> and PbTiO <sub>3</sub> /YBCO/SrTiO <sub>3</sub> Epitaxial Heterostructures," <i>Ferroelectric</i> , Vol. 224, pages 275-282, 1999.
CCAI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.
CCAJ	R. Houdre et al., "Properties of GaAs on Si Grown by Molecular Beam Epitaxy," <i>Solid State and Materials Sciences</i> , Vol. 16, Issue 2, 1990, pp. 91-114.
CCAK	S. F. Fang et al., "Gallium Arsenide and Other Compound Semiconductors on Silicon," <i>J. Appl. Phys.</i> , 68(7), October 1, 1990, pp. R31-R58.
CCAL	Carlin et al., "Impact of GaAs Buffer Thickness on Electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates," <i>Appl. Phys. Letter</i> , Vol. 76, No. 14, April 2000, pp. 1884-1886.
CCAM	Ringel et al., "Epitaxial Integration of III-V Materials and Devices with Si Using Graded GeSi Buffers," <i>27<sup>th</sup> International Symposium on Compound Semiconductors</i> , Oct. 2000.
CCAN	Zogg et al., "Progress in Compound-Semiconductor-on-Silicon-Heteroepitaxy with Fluoride Buffer Layers," <i>J. Electrochem Soc.</i> , Vol. 136, No. 3, March 1998, pp. 775-779.
CCAO	Xiong et al., "Oxide Defined GaAs Vertical-Cavity Surface-Emitting Lasers on Si Substrates," <i>IEEE Photonics Technology Letters</i> , Vol. 12, No. 2, Feb. 2000, pp. 110-112.
CCAP	Clem et al., "Investigation of PZT/LSCO/Pt/Aerogel Thin Film Composites for Uncooled Pyroelectric IR Detectors," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 541, pp. 661-666, 1999.
CCAQ	Gunapala et al., "Bound-To-Quasi-Bound Quantum-Well Infrared Photodetectors," <i>NASA Tech Brief</i> , Vol. 22, No. 9, September 1998.

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449 (Modified)  	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT	ATTY DOCKET NO. 210148US99  APPLICANT Jamal RAMDANI, et al.  FILING DATE June 21, 2001	SERIAL NO. 09/885,409  GROUP 2812
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)			
DDAA	Abhay M. Joshi et al., "Monolithic InGaAs-on-silicon Wave Infrared Detector Arrays," <i>Intn. Society for Optical Engineering</i> , Vol. 2999, pp. 211-224.		
DDAB	Bruley et al., "Nanostructure and Chemistry of a (100)MgO/(100) GaAs Interface," <i>Appl. Phys Lett</i> , 65(5), Aug. 1994, pp. 564-566.		
DDAC	Fork et al., "Epitaxial MgO On Si(001) for Y-Ba-Cu-O Thin Film Growth by Pulsed Laser Deposition," <i>Appl. Phys Lett.</i> , 58(20), May 20, 1991, pp. 2294-2296.		
DDAD	Himpfel et al., "Dialectrics on Semiconductors," <i>Materials Science and Engineering</i> , B1(1988), pp. 9-13.		
DDAE	Li et al., "Epitaxial La <sub>0.67</sub> Sr <sub>0.33</sub> MnO <sub>3</sub> Magnetic Tunnel Junctions," <i>J. Appl. Phys.</i> 81(8), Apr. 15, 1997, pp. 5509-5511.		
DDAF	O'Donnell et al., "Colossal Magnetoresistance Magnetic Tunnel Junctions Grown by Molecular-Beam Epitaxy," <i>Appl. Physics Letters</i> , Vol. 76, No. 14, April 3, 2000, pp. 1914-1916.		
DDAG	Mikami et al., "Formation of Si Epi/MgO-Al <sub>2</sub> O <sub>3</sub> Epi./SiO <sub>2</sub> /Si and Its Epitaxial Film Quality," <i>Fundamental Research Laboratories and Microelectronics Laboratories</i> , pp. 31-34, 1983.		
DDAH	T. Asano et al., "An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF <sub>2</sub> and Silicon," <i>Thin Solid Films</i> , Vol. 93 (1982), pp. 143-150.		
DDAI	T. Chikyow et al., "Reaction and Regrowth Control of CeO <sub>2</sub> on Si(111) Surface for the Silicon-On-Insulator Structure," <i>Appl. Phys. Lett.</i> , Vol. 65, No. 8, 22 August 1994, pp. 1030-1032.		
DDAJ	J.F. Kang, et al., "Epitaxial Growth of CeO <sub>2</sub> (100) Films on Si(100) Substrates by Dual Ion Beams Reactive Sputtering," <i>Solid State Communications</i> , Vol. 108, No. 4, pp. 225-227, 1998.		
DDAK	R.A. Morgan et al., "Vertical-Cavity Surface-Emitting Lasers Come of Age," <i>SPIE</i> , Vol. 2683, pp. 18-29.		
DDAL	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone (Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.		
DDAM	Jo-Ey WONG, et al.; "AN ELECTROSTATICALLY-ACTUATED MEMS SWITCH FOR POWER APPLICATIONS"; IEEE, 2000; pp. 633-638		
DDAN	T. MIZUNO, et al.; "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology"; IEEE ELECTRON DEVICE LETTERS, VOL. 21. NO. 5, MAY 2000; pp. 230-232		
DDAO	F.M. BUFFER, et al.; "Strain-dependence of electron transport in bulk Si and deep-submicron MOSFET's" <i>Computatual Electronics</i> , 2000, Book of Abstracts, IWCE Glasgow 2000, 7 <sup>th</sup> Int'l Workshop on, 2000; pp. 64-65		
DDAP	S.S. LU, et al.; "Piezoelectric field effect transistor (PEFET) using In <sub>0.2</sub> Ga <sub>0.8</sub> As/Al <sub>0.35</sub> Ga <sub>0.65</sub> As/In <sub>0.2</sub> Ga <sub>0.8</sub> As/GaAs Strained layer structure on (111)B GaAs substrate"; <i>ELECTRONICS LETTERS</i> , 12 <sup>th</sup> Ma 1994, Vol. 30, No. 10; pp. 823-825		
DDAQ	Kihong KIM, et al." On-Chip Wireless Interconnection with Integrated Antennas"; 2000 IEEE; pp. 20.2.1-20.3.4		
Examiner	Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

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LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Jamal RAMDANI, et al.

FILING DATE

June 21, 2001

GROUP

2812

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

EEAA	G. PASSIOPOULOS, et al.; "V-BAND SINGLE CHIP, DIRECT CARRIER BPSK MODULATION TRANSMITTER WITH INTEGRATED PATCH ANTENNA"; 1998 IEEE MTT-S DIGEST; pp. 305-308
EEAB	Mau-Chung Frank CHANG, et al.; "RF/Wireless Interconnect for Inter- and Intra-Chip Communications"; Proceedings of the IEEE, Vol. 89, No. 4, April 2001; pp. 456-466
EEAC	The Electronics Industry Report; Prismark; 2001; pp. 111-120
EEAD	J.K. ABROKWAH, et al.; "A Manufacturable Complementary GaAs Process"; GaAs IC Symposium, IEEE, 1993; pp. 127-130
EEAE	H. Nagata, "A Preliminary Consideration of the Growth Behaviour of CeO <sub>2</sub> , SrTiO <sub>3</sub> and SrVO <sub>3</sub> Films on Si Substrate," <i>Thin Solid Films</i> , 224, 1993, pp. 1-3.
EEAF	Nagata et al., "Heteroepitaxial Growth of CeO <sub>2</sub> (001) Films on Si(001) Substrates by Pulsed Laser Deposition in Ultrahigh Vacuum," <i>Jpn. Jour. Appl. Phys.</i> , Vol. 30, No. 6B, June 1991, pp. L1136-L1138.
EEAG	Kado et al., "Heteroepitaxial Growth of SrO Films on Si Substrates," <i>J. Appl. Phys.</i> , 61(6), March 15, 1987, pp. 2398-2400.
EEAH	H. Ishiwara et al., "Epitaxial Growth of Perovskite Type Oxide Films on Substrates"; <i>Materials Research Symposium Proceedings</i> , Vol. 220, pp. 595-600, April 29 - May 3, 1991.
EEAI	J.K. Abrokwa, et al.; "A Manufacturable High-Speed Low-Power Complementary GaAs Process"; Extended Abstracts of the 1994 International Conference on Solid State Devices and Materials, Yokohama, 1994, pp.592-594
EEAJ	C.J. Palmstrom et al.; "Stable and Epitaxial Contacts to III-V Compound Semiconductors"; <i>Contacts to Semiconductors Fundamentals and Technology</i> ; Noyles Publications, 1993; pp.67-150
EEAK	Jayshri SABARINATHAT, et al.; "Submicron three-dimensional infrared GaAs/Al <sub>x</sub> O <sub>y</sub> -based photonic crystal using single-step epitaxial growth"; <i>APPLIED PHYSICS LETTERS</i> , VOLUME 78, NUMBER 20, 14 MAY 2001; pp.3024-3026
EEAL	Philip BALL; "The Next Generation of Optical Fibers"; <i>Technology Review</i> , May 2001; pp.55-61
EEAM	John D. JOANNOPOULOS, et al.; "Molding the Flow of Light"; <i>Photonic Crystals</i> ; Princeton University Press, 1995
EEAN	Thomas F. KRAUSS, et al.; "Photonic crystals in the optical regime - past, present and future"; <i>Progress in Quantum Electronics</i> 23 (1999) 51-96
EEAO	G. H. JIN, et al.; "PLZT Film Waveguide Mach-Zehnder Electrooptic Modulator"; <i>Journal of Lightwave Technology</i> , Vol. 18, No. 6, June 2000; pp.807-812
EEAP	D.E. ASPNES, et al.; "Steps on (001) silicon surfaces"; <i>J. Vac. Sci. Technol. B</i> , Vol. 5, No. 4, Jul/Aug 1987; pp. 939-944
EEAQ	D.M. NEWNS, et al.; "Mott transition field effect transistor"; <i>APPLIED PHYSICS LETTERS</i> , VOLUME 73, NUMBER 6, 10 AUGUST 1998; pp.780-782

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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APPLICANT

Jamal RAMDANI, et al.

FILING DATE

June 21, 2001

GROUP

2812

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

FFAA	Lucent Technologies, Inc. "Arrayed Waveguide Grating Multiplexer/Demultiplexer"; January 2000; 4 pages
FFAB	Hisashi SHICHIJO, et al.; "Co-Integration of GaAs MESFET and Si CMOS Circuits"; IEEE ELECTRON DEVICE LETTERS, VOL. 9, NO. 9, SEPTEMBER 1988; pp.444-446
FFAC	H. SHICHIJO, et al.; "GaAs MESFET and Si CMOS Cointegration and Circuit Techniques"; 1988 IEEE; GaAs IC Symposium - 239-242
FFAD	H. SHICHIJO, et al.; "Monolithic Process for Co-Integration of GaAs and Silicon Circuits"; 1988 IEEE; pp.778-781
FFAE	Z.H. ZHU, et al. "Growth of InGaAs multi-quantum wells at 1.3 m wavelength on GaAs compliant substrates"; APPLIED PHYSICS LETTERS, VOLUME 72, NUMBER 20, 18 MAY 1998; pp.2598-2600
FFAF	Kurt EISENBEISER, et al.; "Metamorphic InAlAs/InGaAs Enhancement Mode HEMT's on GaAs Substrates"; IEEE ELECTRON DEVICE LETTERS, VOL. 20, NO. 10, OCTOBER 1999; pp.507-509
FFAG	Tomonori NAGASHIMA, et al.; "Three-Terminal Tandem Solar Cells With a Back-Contact Type Bottom Cell" Higashifuji Technical Center, Toyota Motor Corporation; 4 pages
FFAH	James SCHELLENBERG, et al.; "Low-Loss, Planar Monolithic Baluns for K/Ka-Band Applications"; 1999 IEEE MTT-S Digest; pp.1733-1736
FFAI	Arnold Leitner et al; "Pulsed Laser Deposition of Superconducting Strontium Titanate Thin-Films"; ; Session K11-Thin Films and Borocarbides; Mixed Session, Wednesday Afternoon; March 19 1997; Room 1202 B, Conv. Center (Abstract)
FFAJ	R.D. VISPUTE; "High quality optoelectronic grade epitaxial AlN films on -Al <sub>2</sub> O <sub>3</sub> , Si and 6H-SiC by pulsed laser deposition"; Thin Solid Films 299 (1997), pp.94-103
FFAK	T. Warren WEEKS, et al.; "GaN thin films deposited via organometallic vapor phase epitaxy on (6H)-SiC(0001) using high-temperature monocrystalline AlN buffer layers" 320 Applied Physics Letters, Vol. 67, No. 3, 17 July 1995, ppl401-403
FFAL	Z. YU, et al.; "Epitaxial oxide thin films on Si(001)*"; J. Vac. Sci. Technol. B. Vol. 18, No. 4, Jul/Aug 2000; pp.2139-2145
FFAM	Gentex Corporate Website; "Photoelectric Smoke Detectors - How They Work; 2001
FFAN	Jeffrey B. Casady, et al.; "A Hybrid 6H-SiC Temperature Sensor Operational from 25 C to 500 C"; IEEE TRANSACTIONS ON COMPONENTS, PACKAGING, AND MANUFACTURING TECHNOLOGY - PART A, VOL. 19, NO. 3, SEPTEMBER 1996; pp. 416-422
FFAO	Ronald W. WAYNANT, et al.; "OPTOELECTRONIC INTEGRATED CIRCUITS"; ELECTRO-OPTICS HANDBOOK, McGraw-Hill, Inc., 1994; Chapter Twenty Seven
FFAP	Antonio MECOZZI, et al.; "The Roles of Semiconductor Optical Amplifiers in Optical Networks"; Optics & Photonics News; March 2001; pp. 37-42
FFAQ	D.A. FRANCIS, et al.; "A single-chip linear optical amplifier"; OFC, 2001; March 17-22, 2001

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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APPLICANT

Jamal RAMDANI, et al.

FILING DATE

June 21, 2001

GROUP

2812

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

GGAA	G. Vogg et al.; "Epitaxial alloy films of zintl-phase $\text{Ca}(\text{Si}_{1-x}\text{Gex})_2$ "; Journal of Crystal Growth 223 (2001); pp. 573-576
GGAB	Peter S. GUILFOYLE, et al.; "Optoelectronic Architecture for High-Speed Switching and Processing Applications"; 1998 The Photonics Design and Applications Handbook; pp. H-399-H-406
GGAC	Gerald B. STRINGFELLOW; "Organometallic Vapor-Phase Epitaxy: Theory and Practice"; Departments of Materials Science and Engineering and Electrical Engineering, University of Utah; Academic Press, 1989
GGAD	M.A. HERMAN, et al.; "Molecular Beam Epitaxy Fundamentals and Current Status"; Springer-Verlag Berlin Heidelberg, 1989, 1996
GGAE	"Integration of GaAs on Si Using a Spinel Buffer Layer", IBM Technical Bulletin, Vol. 30, No. 6, Nov. 1987, p. 365.
GGAF	"GaInAs Superconducting FET," IBM Technical Bulletin, Vol. 36, No. 8, Aug. 1993, p. 655-656.
GGAG	"Epitaxial 3d Structure Using Mixed Spinel," IBM Technical Bulletin, Vol. 30, No. 3, Aug. 1987, p. 1271.
GGAH	Moon et al., "Roles of Buffer Layers in Epitaxial Growth of $\text{SrTiO}_3$ Films on Silicon Substrates," <i>Japan J of Appl. Phys.</i> , Vol. 33, March 1994, pp. 1472-1477.
GGAI	Yodo et al., GaAs Heteroepitaxial Growth on Si Substrates with Thin Si Interlayers <i>in situ</i> Annealed at High Temperatures," 8257b <i>Journal of Vacuum Science &amp; Technology</i> , 1995 May/June, Vol. 13, No. 3, pp. 1000-1005.
GGAJ	Cuomo et al., "Substrate Effect on the Superconductivity of $\text{YBa}_2\text{Cu}_3\text{O}_7$ Thin Films," AIP Conference 1988, pp. 141-148.
GGAK	McKee et al., "Crystalline Oxides on Silicon: The First Five Monolayers," <i>Physical Review Letters</i> , Vol. 81, No. 14, Oct. 1998, pp. 3014-3017.
GGAL	McKee et al., "Molecular Beam Epitaxy Growth of Epitaxial Barium Silicide, Barium Oxide, and Barium Titanate on Silicon," 1991 <i>American Institute of Physics</i> , pp. 782-784, August 13, 1991.
GGAM	Tambo et al., Molecular Beam Epitaxy Growth of $\text{SrTiO}_3$ Films on $\text{Si}(100)-2\times 1$ with $\text{SrO}$ Buffer Layer," <i>Jpn. J. Appl. Phys.</i> , Vol. 37, 1998, pp. 4454-4459.
GGAN	McKee et al., "The MBE Growth and Optical Quality of $\text{BaTiO}_3$ and $\text{SrTiO}_3$ Thin Films on $\text{MgO}$ ," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 341, April 1994, pp. 309-314.
GGAO	McKee et al., " $\text{BaSi}_2$ and Thin Film Alkaline Earth Silicides on Silicon," <i>Appl. Phys. Lett.</i> , 63 (20), Nov. 1993, pp. 2818-2820.
GGAP	McKee et al., "Surface Structures and the Orthorhombic Transformation of Thin Film $\text{BaSi}_2$ on Silicon," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 221, pp. 131-136,
GGAQ	Brian A. FLOYD, et al.; "The projected Power Consumption of a Wireless Clock Distribution System and Comparison to Conventional Distribution Systems"; IEEE, 1999; pp. IITC99-249-IITC99-250

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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Jamal RAMDANI, et al.

FILING DATE

June 21, 2001

GROUP

2812

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

HHAA	Mori et al., "Epitaxial Growth of SrTiO <sub>3</sub> Films on Si(100) Substrates Using a Focused Electron Beam Evaporation Method," <i>Jpn. J. of Appl. Phys.</i> , Vol. 30, No. 8A, Aug. 1991, pp. L1415-L1417.
HHAB	Moon et al., "Growth of Crystalline SrTiO <sub>3</sub> Films on Si Substrates Using Thin Fluoride Buffer Layers and Their Electrical Properties," <i>Jpn. J. of Appl. Phys.</i> , Vol. 33, (1994), pp. 5911-5916.
HHAC	Farrow et al., "Heteroepitaxy of Dissimilar Materials," <i>Mat. Res. Soc. Symposium Proceedings</i> , Vol. 221, pp. 29-34, April 29 - May 2, 1991.
HHAD	Ishiwara et al., "Heteroepitaxy on Silicon: Fundamentals, Structure, and Devices," <i>Mat. Res. Soc., Symposium Proceedings</i> , Vol. 116, pp. 369-374, April 5-8, 1988.
HHA E	Douglas B. Chrisey, et al; Pulsed Laser Deposition of Thin Films; pp. 273-285
HHAF	B.A. Block, et al; "Photoluminescence properties of Er <sup>3+</sup> -doped BaTiO <sub>3</sub> thin films"; <i>Appl. Phys. Lett.</i> 65 (1), 4 July 1994, pp. 25-27
HHAG	Kevin J. Chen et al; "A Novel Ultrafast Functional Device: Resonant Tunneling High Electron Mobility Transistor"; <i>Electron Devices Meeting</i> 1996; IEEE Hong Kong; June 29, 1996; pp. 60-63, XP010210167
HHAH	Wenhua Zhu et al.; "Molecular Beam Epitaxy of GaAs on Si-on-Insulator"; <i>320 Applied Physics Letters</i> 59(1991) 8 July No. 2; pp. 210-212
HHAI	Umesh K. Mishra et al; "Oxide Based Compound Semiconductor Electronics"; <i>Electron Devices Meeting</i> ; 1997; Technical Digest, International; Washington, D.C.; 7-10 December 1997; pp. 545-548
HHAJ	J.M. Daughton et al.; "Applications of Spin Dependent Transport Materials"; <i>J. Phys. D. Appl. Phys.</i> 32(1999) R169-R177
HHAK	Wei Zhang et al.; "Stress Effect and Enhanced Magnetoresistance in La <sub>0.67</sub> Ca <sub>0.33</sub> MnO <sub>3-δ</sub> Films"; <i>Physical Review, B. Condensed Matter</i> ; American Institute of Physics; Vol. 58, No. 21, Part 1; December 1, 1998; pp. 14143-14146
HHAL	Q.-Y. Tong et al.; "IOS-a new type of materials combination for system-on-a chip preparation"; <i>1999 IEEE International SOI Conference</i> , Oct. 1999; pp.104-105
HHAM	T. Kanninen et al.; "Growth of Dielectric 1HfO <sub>2</sub> /Ta <sub>2</sub> O <sub>5</sub> Thin Film Nanolaminate Capacitors By Atomic Layer Epitaxy"; <i>Electrochemical Society Proceedings</i> , U.S. Electrochemical Society; Pennington, N.J.; August 31, 1997; pp. 36-46
HHAN	Myung Bok Lee; "Heteroepitaxial Growth of BaTiO <sub>3</sub> Films on Si by Pulsed Laser Deposition"; <i>Applied Physics Letters</i> ; March 13, 1995; pp. 1331-1333
HHAO	Myung Bok Lee; "Formation and Characterization of Epitaxial TiO <sub>2</sub> and BaTiO <sub>3</sub> /TiO <sub>2</sub> Films on Si Substrate"; <i>Japan Journal Applied Physics Letters</i> ; Vol. 34; 1995; pp. 808-811
HHAP	Gilbert Lecarpentier et al.; "High Accuracy Machine Automated Assembly for Opto Electronics"; <i>2000 Electronic Components and Technology Conference</i> ; pp. 1-4
HHAQ	R. Ramesh; "Ferroelectric La-Sr-Co-O/Pb-Zr-Ti-O/La-Sr-Co-O Heterostructures on Silicon via Template Growth"; <i>320 Applied Physics Letters</i> ; 63(1993); 27 December; No. 26; pp. 3592-3594

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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## LIST OF REFERENCES CITED BY APPLICANT

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Jamal RAMDANI, et al.

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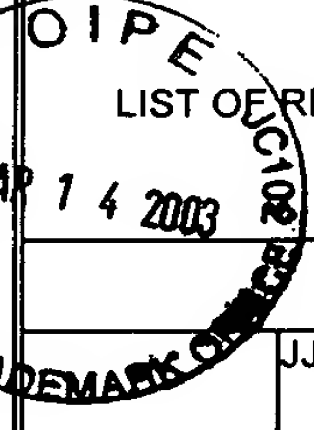
## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

IIAA	K. Eisenbeiser; "Field Effect Transistors with SrTiO <sub>3</sub> Gate Dielectric on Si"; Applied Physics Letters; Vol. 76, No. 10; March 6, 2000; pp. 1324-1326
IIAB	Stephen A. Mass; "Microwave Mixers"; Second Edition; 2pp.
IIAC	Douglas J. Hamilton et al.; "Basic Integrated Circuit Engineering"; pp.2; 1975
IIAD	Takeshi Obata; "Tunneling Magnetoresistance at Up to 270 K in La <sub>0.8</sub> Sr <sub>0.2</sub> MnO <sub>3</sub> /SrTiO <sub>3</sub> /La <sub>0.8</sub> Sr <sub>0.2</sub> MnO <sub>3</sub> Junctions with 1.6-nm-Thick Barriers"; Applied Physics Letters; Vol. 74, No. 2; 11 January 1999; pp. 290-292
IIAE	Wei Zhang et al.; "Enhanced Magnetoresistance in La-Ca-Mn-O Films on Si Substrates Using YbaCuO/CeO <sub>2</sub> Heterostructures"; Physica C; Vol. 282-287, No. 2003; 1 August 1997; pp. 1231-1232
IIAF	Shogo Imada et al.; "Epitaxial Growth of Ferroelectric YmnO <sub>3</sub> Thin Films on Si (111) Substrates by Molecular Beam Epitaxy"; Jpn. J. Appl. Phys. Vol. 37 (1998); pp. 6497-6501; Part 1, No. 12A, December 1998
IIAG	Ladislav Pust et al.; "Temperature Dependence of the Magnetization Reversal in Co(fcc)-BN-Co(poly hcp) Structures"; Journal of Applied Physics; Vol. 85, No. 8; 15 April 1999; pp. 5765-5767
IIAH	C. Martinez; "Epitaxial Metallic Nanostructures on GaAs"; Surface Science; Vol. 482-485; pp. 910-915; 2001
IIAI	Wen-Ching Shih et al.; "Theoretical Investigation of the SAW Properties of Ferroelectric Film Composite Structures"; IEEE Transactions of Ultrasonics, Ferroelectrics, and Frequency Control; Vol. 45, No. 2; March 1998; pp. 305-316
IIAJ	Zhu Dazhong et al.; "Design of ZnO/SiO <sub>2</sub> /Si Monolithic Integrated Programmable SAW Filter"; Proceedings of Fifth International Conference on Solid-State and Integrated Circuit Technology; 21-23; October 1998; pp. 826-829
IIAK	Kirk-Othmer Encyclopedia of Chemical Technology; Fourth Edition, Vol. 12; Fuel Resources to Heat Stabilizers; A Wiley-Interscience Publication; John Wiley & Sons
IIAL	Joseph W. Goodman et al.; "Optical Interconnections For VLSI Systems"; Proceedings of the IEEE, Vol. 72, No. 7 July 1984
IIAM	Fathimulla et al.; "MONOLITHIC INTEGRATION OF InGaAs/InAlAs MODFETs and RTDs on InP-bonded-to Si SUBSTRATE"; Fourth International Conference on Indium Phosphide and Related Materials, Newport, RI, USA; April 21-24, 1992; pp. 167-170; XP000341253; IEEE, New York, NY, USA; ISBN: 0-7803-0522-1
IIAN	H. Takahashi et al.; "Arrayed-Waveguide Grating For Wavelength Division Multi/Demultiplexer With Nanometre Resolution"; Electronics Letters; Vol. 26., No. 2, 18th January 1990
IIAO	Pierret, R.F.; "1/J-FET and MESFET"; Field Effect Devices; MA, Addison-Wesley; 1990; pp. 9-22
IIAP	M. Schreiter, et al.; "Sputtering of Self-Polarized PZT Films for IR-Detector Arrays"; 1998 IEEE; pp. 181-185
IIAQ	Hideaki Adachi et al.; "Sputtering Preparation of Ferroelectric PLZT Thin Films and Their Optical Applications"; IEEE Transactions of Ultrasonics, Ferroelectrics and Frequency Control, Vol. 38, No. 6, November 1991

Examiner

Date Considered

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 LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	JJAA	A.J. Moulson et al.; "Electroceramics Materials Properties Applications"; Chapman & Hall; pp. 366-369					
	JJAB	P.A. Langjahr et al.; "Epitaxial Growth and Structure of Cubic and Pseudocubic Perovskite Films on Perovskite Substrates"; Mat. Res. Soc. Symp. Proc., Vol. 401; 1995 Materials Research Society; pp. 109-114					
	JJAC	Wang et al.; "Depletion-Mode GaAs MOSFETs with Negligible Drain Current Drift and Hysteresis"; Electron Devices Meeting, 1998, IEDM '98 Technical Digest; pp. 67-70					
	JJAD	Ben G. Streetman; "Solid State Electronic Devices"; 1990, Prentice Hall; Third Edition; pp. 320-322					
	JJAE	A.Y Wu et al.; "Highly Oriented (Pb,La)(Zr,Ti)O <sub>3</sub> Thin Films on Amorphous Substrates"; IEEE, 1992; pp. 301-304					
	JJAF	Timothy E. Glassman et al.; "Evidence for Cooperative Oxidation of MoCVD Precursors Used in Ba <sub>x</sub> Sr <sub>1-x</sub> TiO <sub>3</sub> Film Growth"; Mat. Res. Soc. Symp. Proc. Vol. 446, 1997 Materials Research Society; pp. 321-326					
	JJAG	S.N. Subbarao et al.; "Monolithic PIN Photodetector and FET Amplifier on GaAs-os-Si"; IEEE; GaAs IC Symposium-163-166; 1989					
	JJAH	T.A. Langdo et al.; "High Quality Ge on Si by Epitaxial Necking"; Applied Physics Letters; Vol. 76, No. 25; pp. 3700-3702; June 19, 2000					
	JJAI	Chenning Hu et al.; Solar Cells From Basics to Advanced Systems; McGraw-Hill Book Company; 1983					
	JJAJ	O.J. Painter et al; "Room Temperature Photonic Crystal Defect Lasers at Near-Infrared Wavelengths in InGaAsp"; Journal of Lightwave Technology, Vol. 17, No. 11; November 1999					
	JJAK	C. Donn et al.; "A 16-Element, K-Band Monolithic Active Receive Phased Array Antenna"; Antennas and Propagation Society International Symposium, 1988; pp.188-191, Vol. 1; 6-10 June 1988					
	JJAL	Don W. Shaw; "Epitaxial GaAs on Si: Progress and Potential Applications"; Mat. Res. Soc. Symp. Proc.; pp.15-30; 1987					
	JJAM	G.J.M. Dormans, et al.; "PbTiO <sub>3</sub> /Thin Films Grown by Organometallic Chemical Vapour Deposition"; Third International Symposium on Integrated Ferroelectrics; April 3-5, 1991 (Abstract)					
	JJAN	P.J. Borrelli et al.; "Compositional and Structural Properties of Sputtered PLZT Thin Films"; Ferroelectric Thin Films II Symposium; Dec. 2-4, 1991 (Abstract)					
	JJAO	Ranu Nayak et al; "Enhanced acousto-optic diffraction efficiency in a symmetric SrTiO <sub>3</sub> /BaTiO <sub>3</sub> /SrTiO <sub>3</sub> thin-film heterostructure"; 1 November 2000; Vol. 39, No. 31; Applied Optics; pp. 5847-5853					
	JJAP	Ranu Nayak et al; "Studies on acousto-optical interaction in SrTiO <sub>3</sub> /BaTiO <sub>3</sub> /SrTiO <sub>3</sub> epitaxial thin film heterostructures"; J. Phys. D: Appl. Phys. 32 (1999) 380-387					
	JJAQ	S.K. Tewksbury et al.; "Cointegration of Optoelectronics and Submicron CMOS"; Wafer Scale Integration; 1993; Proceedings, Fifth Annual IEEE; 20 January 1993; pp. 358-367					
Examiner				Date Considered			
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## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

KKAA	V. Kaushik et al.; "Device Characteristics of Crystalline Epitaxial Oxides on Silicon"; Device Research Conference, 2000; Conference Digest 58th DRC; pp. 17-20; June 19-21, 2000
KKAB	Katherine Derbyshire; "Prospects Bright for Optoelectronics Volume, Cost Drive Manufacturing for Optical Applications"; Semiconductor Magazine; Vol. 3, No. 3; March 2002
KKAC	Alex Chediak et al; "Integration of GaAs/Si with Buffer Layers and Its Impact on Device Integration"; TICS 4, Prof. Sands. MSE 225, April 12, 2002; pp. 1-5
KKAD	S.A. Chambers et al; "Band Discontinuities at Epitaxial SrTiO <sub>3</sub> /Si(001) Heterojunctions"; Applied Physics Letters; Vol. 77, No. 11; September 11, 2000; pp. 1662-1664
KKAE	H. Wang et al.; "GaAs/GaAlAs Power HBTs for Mobile Communications"; Microwave Symposium Digest; 1993 IEEE; Vol. 2.; pp. 549-552
KKAF	Y. Ota et al.; "Application of Heterojunction FET to Power Amplifier for Cellular Telephone"; Electronics Letters; 26th May 1994; Vol. 30, No. 11; pp. 906-907
KKAG	Keiichi Sakuno et al; "A 3.5W HBT MMIC Power Amplifier Module for Mobile Communications"; IEEE 1994; Microwave and Millimeter-Wave Monolithic Circuits Symposium; pp. 63-66
KKAH	Mitsubishi Semiconductors Press Release (GaAs FET's) November 8, 1999 pp.1-2
KKAI	R.J. Matyi et al; "Selected Area Heteroepitaxial Growth of GaAs on Silicon for Advanced Device Structures"; 2194 Thin Solid Films; 181 (1989) December 10; No. 1; pp. 213-225
KKAJ	K. Nashimoto et al; "Patterning of Nb, LaOnZr, TiO <sub>3</sub> Waveguides for Fabricating Micro-Optics Using Wet Etching and Solid-Phase Epitaxy"; Applied Physics Letters; Vol. 75, No. 8; 23 August 1999; pp. 1054-1056
KKAK	Bang-Hung Tsao et al; "Sputtered Barium Titanate and Barium Strontium Titanate Films for Capacitor Applications"; Applications of Ferroelectrics, 2000; Proceedings of the 2000 12th International Symposium on Vol. 2; pp. 837-840
KKAL	Man Fai Ng et al; "Heteroepitaxial growth of lanthanum aluminate films derived from mixed metal nitrates"; Journal of Materials Research; Vol. 12, No. 5; pp. 1306
KKAM	Yuji Matsumoto et al.; "Room-Temperature Ferromagnetism in Transparent Transition Metal-Doped Titanium Dioxide"; Science; 2 February 2001; Vol. 291; pp. 854-856
KKAN	S.A. Chambers et al.; "Epitaxial Growth and Properties of Ferromagnetic Co-Doped TiO <sub>2</sub> Anatase"; Applied Physics Letters; Vol. 79, No. 21; November 19, 2001; pp. 3467-3469
KKAO	
KKAP	
KKAQ	

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